GaN Power Device Manufacturers[1]

2013

Suppliers	Epi substrate	Wafer size	Transistor type	Max. voltage (V)	Diode	Max. voltage (V)
Avogy	Gallium nitride	2 in. (50 mm)	Enhancement-mode vertical JFET	1200	Schottky PN	600 (Schottky) 1700 (PN)
Efficient Power Conversion	Silicon	6 in.	Enhancement-mode FET	200 100 40	--	--
Fuji Electric	--	--	--	--	Schottky	600
Fujitsu Semiconductor	Silicon	6 in.	--	--	--	--
GaN Systems	Silicon carbide	3 (75 mm) and 4 in. (100 mm)	Depletion-mode HEMT*	600	--	--
International Rectifier	Silicon	6 in. (150 mm)	Depletion-mode HEMT[2]	600	--	--
NXP Semiconductor	Silicon	--	--	--	Schottky	650
ON Semiconductor	--	--	--	--	--	--
Panasonic	Silicon	6 in.	Normally-off gate injection transistor (GIT)	600	--	--
Power Wafers Development	Sapphire	--	--	--	Schottky	600
RF Micro Devices	Silicon carbide	4 in.	Source switched FET	650	--	--
Sameo	--	--	--	--	--	--
STMicroelectronics	Silicon	6 in.	Enhancement-mode HEMT	200	--	--
Transphorm	Silicon	6 in.	HEMT	600	Schottky	600

Notes:1) This chart originally appeared in "GaN Power Devices Transition To Production Phase," by Ashok Bindra, How2Power Today, June 2013 issue. 2) Offered in cascode form.

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